

EAST - [10621050.wsp:1]

File View Edit Tools Window Help

L11: (0) 10 and (passivation).ti.  
L12: (6) 10 and (passivation).ab.  
L13: (55) 10 not 12  
L14: (6) 13 and (passivation).clm.  
L15: (49) 13 not 14  
L16: (5) 15 and (sputter\$4 with passivation)  
L17: (237) (ferroelectr\$4 or magnet\$4) and (sputter\$4  
L18: (16) 17 and ((Aluminum or "Al") and (Titanium or  
L19: (12) 18 not (2 8 9 12 14 16)  
L20: (170) (ferroelectr\$4 or magnet\$4) and ((Aluminum or  
L21: (145) 20 not (2 8 9 12 14 16 19)  
L22: (95) 21 and (electrode)  
L23: (45) 22 and chamber  
L24: (2) (ferroelectr\$4 or magnet\$4) and ("Al-Ti-O" or  
Failed

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Browse Queue Clear  
Dbs: USPAT, USPGPUE, EPO, JPO, IBM, TDB  
Default operator: OR  
 BSearch  
 Highlight hit terms initially

17 and (((Aluminum or "Al") and (Titanium or "Ti")) with passivation)

U	I	P	T	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020140011	20021003	9	Method of using titanium doped aluminum oxide for passivation of ferroelectric materials and	257/295	257/E21.009; 257/E21.274; 257/E21.281;	<input checked="" type="checkbox"/>	Zhang, Fengyan et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6630702	20031007	9	Method of using titanium doped aluminum oxide for passivation of ferroelectric materials and	257/295	257/306; 257/E21.009; 257/E21.274;	<input checked="" type="checkbox"/>	Zhang, Fengyan et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6573169	20030603	16	Highly conductive composite polysilicon gate for CMOS integrated circuits	438/592	438/585; 438/594	<input checked="" type="checkbox"/>	Noble, Wendell P. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6492694	20021210	16	Highly conductive composite polysilicon gate for CMOS integrated circuits	257/410	257/411; 257/412; 257/413;	<input checked="" type="checkbox"/>	Noble, Wendell P. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6413863	20020702	11	Method to resolve the passivation surface roughness during formation of the AlCu pad for the	438/687	257/E21.31; 257/E21.311; 257/E21.508;	<input checked="" type="checkbox"/>	Liu, Chung-Shi et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6333528	20011225	25	Semiconductor device having a capacitor exhibiting improved moisture resistance	257/295	257/296; 257/532; 257/535;	<input checked="" type="checkbox"/>	Arita, Koji et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6294438	20010925	26	Semiconductor device having a capacitor and manufacturing method thereof	438/396	257/E21.008; 257/E21.009; 257/E21.011;	<input checked="" type="checkbox"/>	Arita, Koji et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6229167	20010508	15	Semiconductor device and method of manufacturing the same	257/295	257/296; 257/300; 257/532;	<input checked="" type="checkbox"/>	Ozawa, Takanori	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6169304	20010102	25	Semiconductor device having a passivation layer which minimizes	257/295	257/296; 257/532;	<input checked="" type="checkbox"/>	Arita, Koji et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>

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L Number	Hits	Search Text	DB	Time stamp
1	278	(form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)	USPAT	2004/03/21 18:29
2	350	zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/03/21 18:22
3	277	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/03/21 18:22
4	69	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/03/21 18:24
5	2	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3"))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/03/21 18:29
6	67	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/03/21 18:29
7	0	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and ((form\$4 or creat\$4) adj (passivation adj layer)).ti.	USPAT	2004/03/21 18:30
8	0	((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and ((form\$4 or creat\$4) adj (passivation adj layer)).ab.	USPAT	2004/03/21 18:30

9	6	(((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and ((form\$4 or creat\$4) adj (passivation adj layer)).clm.	USPAT	2004/03/21 19:05
10	61	(((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and ((form\$4 or creat\$4) adj (passivation adj layer)).clm.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 19:06

11	0	(((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and (((form\$4 or creat\$4) adj (passivation adj layer)).clm.)) and (passivation).ti.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 19:06
12	6	(((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) not (((((form\$4 or creat\$4) adj (passivation adj layer) and (ferroelect\$4 or magnet\$4)) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber) and (aluminum or "Al") and (titanium or "Ti")) and (((titanium adj oxide) or "TiO.sub.2") and ((aluminum adj oxide) or "Al.sub.20.sub.3")))) and (((form\$4 or creat\$4) adj (passivation adj layer)).clm.)) and (passivation).ab.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 19:12









17	237	(ferroelectr\$4 or magnet\$4) and (sputter\$4 with passivation)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 19:37
18	16	((ferroelectr\$4 or magnet\$4) and (sputter\$4 with passivation)) and (((Aluminum or "Al") and (Titanium or "Ti")) with passivation)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 19:25



20	170	(ferroelectr\$4 or magnet\$4) and ((Aluminum or "Al") and (Titanium or "Ti") with passivation)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/03/21 20:41
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24	2	(ferroelectr\$4 or magnet\$4) and ("Al-Ti-O" or "Al--Ti--O")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/21 20:42
-	0	"2001/0034106".PN.	USPAT	2004/03/21 18:20
-	0	bhang-fengyan.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	122	zhang-fengyan.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	306	hsu-sheng-teng.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	13	ying-hong.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	5	(titanium near2 aluminum near2 passivation) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	0	((titanium near2 aluminum near2 passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:23
-	573	((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	266	((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	87	((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	0	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ti.) not (((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	1	"6630702"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	580	(titanium and aluminum and passivation) and ferroelectric	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
-	5	(zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.) and ((titanium near2 aluminum near2 passivation))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24

	2	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ti.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:24
	2	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.) not (((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ti.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:30
	411	ferroelectric and passivation and chamber	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:31
	345	(ferroelectric and passivation and chamber) and electrode	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:31
	236	((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:32
	230	((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) not (((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) and (((("Al" or aluminum) and ("Ti"or Titanium)) with passivation))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:54
	16	((((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) not (((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) and (((("Al" or aluminum) and ("Ti"or Titanium)) with passivation)) and (aluminum adj oxide) and (titanium adj oxide))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/19 17:56
	23	(method or process) and (ferroelectric) and electrode and chamber and ((Titanium adj oxide) or "Ti.sub.2 O.sub.3") and ((aluminum adj oxide) or "Al.sub.2 O.sub.3") and passivation	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:34
	4	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:35
	3	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.clm.) not (((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:36

		6	(((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:36
		6	((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium) and (((Al" or aluminum) and ("Ti"or Titanium)) with passivation)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:36
		7	((((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) not (((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) and (((Al" or aluminum) and ("Ti"or Titanium)) with passivation))) and (aluminum adj oxide) and (titanium adj oxide)) and (sputter\$4 near3 ((aluminum or "Al") and (titanium or "Ti"))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:36
		14	((method or process) and (ferroelectric) and electrode and chamber and ((Titanium adj oxide) or "Ti.sub.2 O.sub.3") and ((aluminum adj oxide) or "Al.sub.2 O.sub.3") and passivation) not ((((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.) (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.) ((((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.clm.) not ((((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.ab.)) ((((((titanium and aluminum and passivation) and ferroelectric) not (zhang-fengyan.in. hsu-sheng-teng.in. ying-hong.in.)) and (chamber and (method or process))) and ((top or upper) adj electrode)) and passivation.clm.) (((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) and (((Al" or aluminum) and ("Ti"or Titanium)) with passivation)) (((((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)). not (((ferroelectric and passivation and chamber) and electrode) and ("Al" or aluminum) and ("Ti"or Titanium)) and (((Al" or aluminum) and ("Ti"or Titanium)) with passivation))) and (aluminum adj oxide) and (titanium adj oxide)) and (sputter\$4 near3 ((aluminum or "Al") and (titanium or "Ti")))))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/20 18:37